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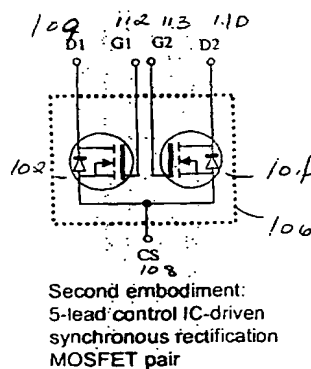
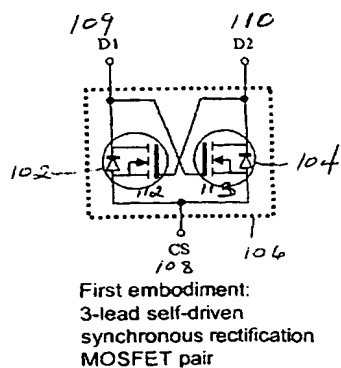
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(54) Title: **MONOLITHIC POWER SEMICONDUCTOR STRUCTURES**



(57) Abstract: Provided herein are exemplary embodiments of monolithic semiconductor structures having at least two lateral constructed semiconductor devices combined on a single semiconductor substrate.

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